



DMN2310U

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
	175mΩ @ V <sub>GS</sub> = 4.5V	1.6A
20V	240m $\Omega$ @ V <sub>GS</sub> = 2.5V	1.3A
	360mΩ @ VGs = 1.8V	1.1A

### Description

This new generation MOSFET has been designed to minimize the onstate resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

Load Switch

## N-CHANNEL ENHANCEMENT MODE MOSFET

### Features

- Low Gate Threshold Voltage
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

## **Mechanical Data**

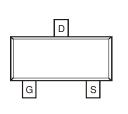
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (c3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

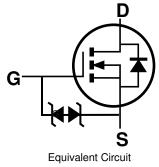




SOT23

Top View





Top View Pin-Out

# Ordering Information (Note 4)

	Part Number	Case	Packaging			
	DMN2310U-7	SOT23	3000/Tape & Reel			
	DMN2310U-13	SOT23	10000/Tape & Reel			
Notes:	Notes: 1. No purposelv added lead. Fully EU Directive 2002/95/EC (RoHS). 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.					

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**

HD2	ΜY

 $\begin{array}{l} HD2 = \mbox{Product Type Marking Code} \\ \overline{Y}\mbox{M or } YM = \mbox{Date Code Marking} \\ \overline{Y} \mbox{ or } Y = \mbox{Year (ex: G = 2019)} \\ M = \mbox{Month (ex: 9 = \mbox{September)}} \end{array}$ 

Date Code Key												
Year	2019	20	20	2021	2022	20	23	2024	2025	20	026	2027
Code	G	ł	4		J	ł	<	L	М		N	0
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	20	V		
Gate-Source Voltage	Vgss	±8	V		
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$	lD	1.6 1.2	А
Maximum Continuous Body Diode Forward Curren	ls	0.82	A		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	I <sub>DM</sub>	4.8	A		

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.48	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	260	°C/W
Total Power Dissipation (Note 6)		PD	0.68	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>0JA</sub>	184	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

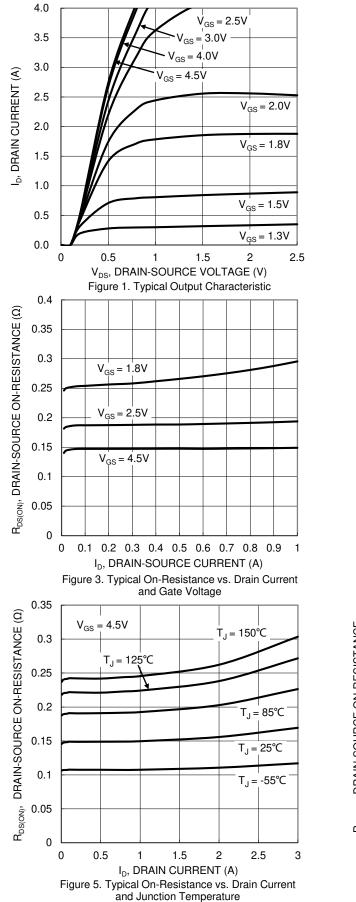
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BVDSS	20	_	_	V	$V_{GS} = 0V, I_{D} = 250 \mu A$		
Zero Gate Voltage Drain Current TJ = +25°C	IDSS	_	_	1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$		
Gate-Source Leakage	lgss	_	_	10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	VGS(TH)	0.45	—	0.95	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$		
			140	175		Vgs = 4.5V, ID = 300mA		
Static Drain-Source On-Resistance	RDS(ON)	—	180	240	mΩ	$V_{GS} = 2.5V, I_{D} = 250mA$		
			245	360		Vgs = 1.8V, ID = 100mA		
Diode Forward Voltage	Vsd	_	0.8	1.2	V	Vgs = 0V, Is = 1A		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	Ciss	_	38	_	pF			
Output Capacitance	Coss	_	10	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz		
Reverse Transfer Capacitance	Crss		6	—	pF	1 - 1.00012		
Total Gate Charge	Qg	_	0.7	_	nC			
Gate-Source Charge	Q <sub>gs</sub>	_	0.1	_	nC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 6A		
Gate-Drain Charge	Qgd		0.1		nC			
Turn-On Delay Time	t <sub>D(ON)</sub>		8	_	ns			
Turn-On Rise Time	tR		138		ns	$V_{DD} = 10V, V_{GS} = 5V,$		
Turn-Off Delay Time	tD(OFF)	_	154		ns	$R_L = 1.7\Omega, R_G = 6\Omega$		
Turn-Off Fall Time	tF	_	180		ns	7		

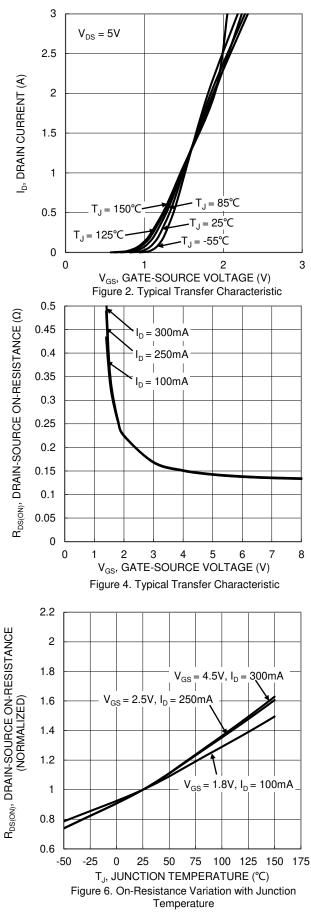
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Borice mounted on FR-4 substrate PC board, 2oz copper, with 1 inch square copper plate.
Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

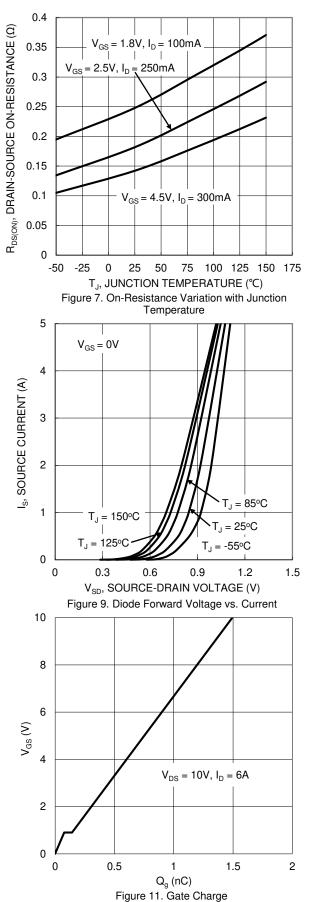


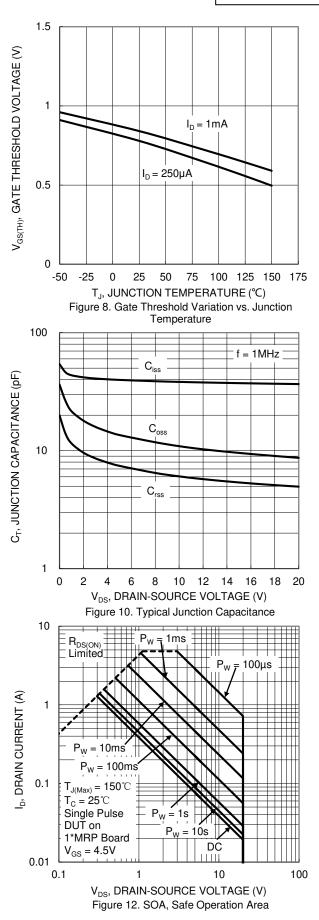






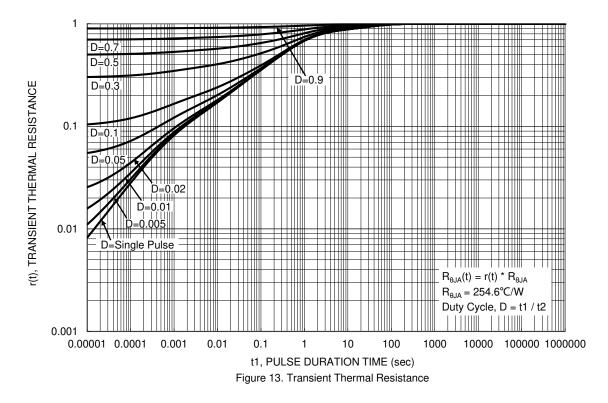






DMN2310U Document number: DS41828 Rev. 2 - 2





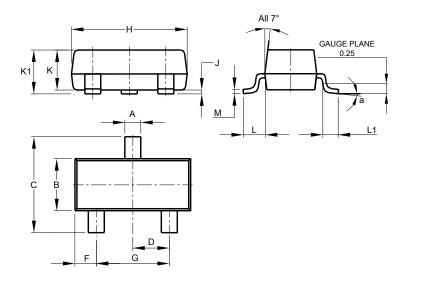


## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

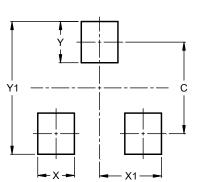
SOT23



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
К	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All	Dimens	ions in	mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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